

L Num b r	Hits	S arch Text	DB	Tim stamp
1	2	("5918113").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/28 21:14
-	31	((("5013119") or ("1013002") or ("1084014") or ("1199930") or ("6283225") or ("9161544") or ("9293414") or ("1135567"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:15
-	23	"05013119" "01013002" "01084014" "01199930" "06283225" "09161544" "09293414" "01135567"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:24
-	0	"090161544"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:24
-	0	("9161544").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:25
-	0	("90161544").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:25
-	0	"090161544"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:25
-	0	"9161544"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:25
-	0	("9161544").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 20:32
-	1	1993-062929.NRAN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2003/10/15 20:46

-	2	"10013002"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2003/10/16 16:17
-	1	1998-136816.NRAN.	DERWENT	2003/10/15 21:39
-	1	1993-062929.NRAN.	DERWENT	2003/10/15 21:40
-	2	5013119.URPN.	USPAT	2003/10/15 21:40
-	0	10013002.URPN.	USPAT	2003/10/15 21:41
-	0	10013002.URPN.	USPAT	2003/10/15 21:41
-	2835	metamorph\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:17
-	367133	epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:17
-	3	metamorph\$ adj epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 21:06
-	56790	thickness near direction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 21:56
-	0	"090306573"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 21:56
-	2	"09306573"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 22:03
-	1	1998-068875.NRAN.	DERWENT	2003/10/16 21:57
-	2	"10199930"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:43

-	1	1998-473136.NRAN.	DERWENT	2003/10/16 22:03
-	0	10199930.URPN.	USPAT	2003/10/16 22:04
-	48513	elastic\$ near modulus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:44
-	49722	cte (coefficient near thermal near expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	247456	(first second) adj2 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	139550	two adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	302	438/188,119.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	344248	((first second) adj2 layer) (two adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:47
-	118531	anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:47
-	2901	(elastic\$ near modulus) and (cte (coefficient near thermal near expansion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:48
-	344	anisotrop\$ and ((elastic\$ near modulus) and (cte (coefficient near thermal near expansion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:48

-	118	(((first s nd) adj2 layer) (two adj lay r)) and (anis tr p\$ and ((elastic\$ n ar modulus) and (cte (coeffici nt near thermal n ar expansion))))	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:48
-	0	438/188,119.ccls. and (((first second) adj2 layer) (two adj layer)) and (anisotrop\$ and ((elastic\$ near modulus) and (cte (coefficient near thermal near expansion))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:48
-	1721521	semiconductor integrated adj circuit ic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:49
-	81	((((first second) adj2 layer) (two adj layer)) and (anisotrop\$ and ((elastic\$ near modulus) and (cte (coefficient near thermal near expansion)))) and (semiconductor integrated adj circuit ic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:49
-	4709545	@ad>19990217 @rlad>19990217 @pt1d>19990217	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:49
-	24	((((first second) adj2 layer) (two adj layer)) and (anisotrop\$ and ((elastic\$ near modulus) and (cte (coefficient near thermal near expansion)))) and (semiconductor integrated adj circuit ic)) not (@ad>19990217 @rlad>19990217 @pt1d>19990217)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:31
-	527040	silica\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:50
-	6	silica\$ and (((((first second) adj2 layer) (two adj layer)) and (anisotrop\$ and ((elastic\$ near modulus) and (cte (coefficient near thermal near expansion)))) and (semiconductor integrated adj circuit ic)) not (@ad>19990217 @rlad>19990217 @pt1d>19990217))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:50
-	35241	double adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:31

-	370236	((first second) adj2 layer) (two adj layer)) r (double adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:47
-	1	ac8301	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:48
-	5554	((first second) adj2 layer) (two adj layer)) or (double adj layer)) with anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:48
-	4319	(semiconductor integrated adj circuit ic) and (((first second) adj2 layer) (two adj layer)) or (double adj layer)) with anisotrop\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:48
-	2	((elastic\$ near modulus) and (cte (coefficient near thermal near expansion))) and ((semiconductor integrated adj circuit ic) and (((first second) adj2 layer) (two adj layer)) or (double adj layer)) with anisotrop\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 20:59
-	2	(((((first second) adj2 layer) (two adj layer)) or (double adj layer)) with anisotrop\$) and (elastic\$ near modulus) and (cte (coefficient near thermal near expansion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 21:01
-	56790	thickness near direction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 21:01
-	1338	anisotrop\$ with (thickness near direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 21:01
-	210	(anisotrop\$ with (thickness near direction)) and (((first second) adj2 layer) (two adj layer)) or (double adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 21:04
-	111	((anisotrop\$ with (thickness near direction)) and (((first second) adj2 layer) (two adj layer)) r (double adj layer))) and (semiconductor integrated adj circuit ic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 21:04

-	57	(((anisotr p\$ with (thi kness n ar directi n)) and (((first sec nd) adj2 lay r) (two adj lay r)) r (double adj layer))) and (s mic nduct r integrated adj ircuit i)) not (@ad>19990217 @rlad>19990217 @pt1d>19990217)	U PAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 21:05
-	7	(US-5120665-\$ or US-5001542-\$ or US-4977007-\$ or US-6172878-\$ or US-6042894-\$ or US-6034331-\$ or US-5438223-\$).did.	USPAT	2003/10/17 21:44
-	2486	underfil\$	USPAT	2003/10/17 21:45
-	77	((elastic\$ near modulus) and (cte (coefficient near thermal near expansion))) and underfil\$	USPAT	2003/10/17 21:45
-	37	(((elastic\$ near modulus) and (cte (coefficient near thermal near expansion))) and underfil\$) not (@ad>19990217 @rlad>19990217 @pt1d>19990217)	USPAT	2003/10/17 21:45
-	3	"01135567"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 16:40
-	7	("1135567").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 14:45
-	7	"1120449"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 16:44
-	7	("1120449").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 16:44